Flux pinning properties of superconductors with an array of blind holes

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We perform ed ac-susceptibility measurements to explore the vortex dynamics and the ux pinning properties of superconducting Pb lm s with an array of micro-holes (antidots) and non-fully perforated holes (blind holes). A lower ac-shielding together with a smaller extension of the linear regime for the lattice of blind holes indicates that these centers provide a weaker pinning potential than antidots. Moreover, we found that the maximum number of ux quanta trapped by a pinning site, ie. the saturation number n_s , is lower for the blind hole array.

I. IN TRODUCTION

The latest advances of lithographic techniques based on electron beam shave allowed to design and tailor arti cialpinning centers in type II superconductors practically at will. In particular, it has been shown that periodically distributed pinning centers lead to a strong reduction of the vortex m obility and consequently to a substantial increase of the critical current when the ux line lattice is commensurate with the pinning array.^{1,2,3,4,5,6,7} So far, most of the work has been devoted to arrays of holes (antidots)^{2,3,4} and m agnetic dots.^{5,6,7} H ow ever, m uch less attention has been paid to the analysis of blind hole arrays. Unlike antidots, these non-fully perforated holes have a thin superconducting bottom layer which allows the trapped ux to remain as separated single quantum vortices inside the pinning site. A direct con mation of this behavior was reported by Bezryadin et al.⁸ who used vortex im aging by m eans of B itter decoration. On top of that, a blind hole sam ple represents a singly-connected system while an antidot sample is a multiply-connected one. As has been pointed out by M oshchalkov et al^{2,3} this topological consideration might also lead to di erences in the irreversible response.

In this work we perform a comparative study of the vortex dynamic response in type II superconducting Pb

In s with an array of blind holes and antidots, by acsusceptibility measurements.^{9,10} W e found that blind holes are lesse cient pinning centers than antidots. This e ect manifests itself as a lower ac-shielding and consequently as a smaller extension of the linear regime. Additionally, we show that the maximum number of ux quanta, n_s ,^{11,12,13} trapped by a blind hole is system atically lower than for an antidot.

II. EXPERIMENTAL ASPECTS

A. Sam ple preparation

The used nanostructured superconducting Pb lms were prepared as follows: rst, a superconducting Pb layer is deposited on a Si/SiO₂ substrate covered by a

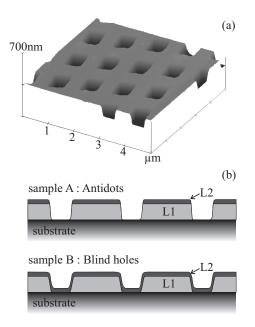
TABLE I: Thicknesses of Pb layers L1 and L2 for the two sets of studied sam ples.

	set 1	set 2
L1	47 . 5 nm	75 nm
L2	13,5 nm	25 nm

double (PMMAnMMA) resist layer in which a square lattice of square dots is prede ned by electron-beam lithography (Im ec vzw). The Pb layer is deposited in a molecular-beam epitaxy system at a working pressure of 7 $\,10^{-8}$ Torr. In order to obtain a sm ooth Pb lm the substrate is cooled by liquid nitrogen (77 K) and the

Im is evaporated at a grow th rate of 5A /s, controlled by a quadrupole m ass spectrom eter. A fter the evaporation, the remaining resist is removed by a lift-o procedure using warm aceton. The double resist layer has an overhanging pro lew hich avoids any contact of the deposited material on top of the resist dots with material between the dots. The nal result is a Pb Im with a square lattice of square holes. For the protection of the Pb sam ples against oxidation a 70 nm -thick Ge capping layer is nally evaporated on top of the Im. In order to grow the antidot and the blind hole sam ples simultaneously, we rst deposit a Pb layer (L1) on top of two identical resist dot patterns. Then, for one of them (sam ple B in Fig. 1(b)) we carry out a lift-o procedure whereas the other (sam ple A in Fig. 1 (b)) rem ains unchanged. A fter that, a second Pb layer (L2) is deposited on top of both samples. Finally, the resist on sample A is removed by lift-o . In this way we end up with an antidot sample (sam ple A) which has exactly the sam e thickness as the blind holes (sam ple B) and has been grown under identical conditions.

The data presented in this work were obtained from two sets of blind and antidot sam ples. Each fam ily has a di erent total thickness as determ ined by low -angle X -ray di raction. In Table I we give the thicknesses of the subsequently evaporated Pb layers, L1 and L2, for the two studied sets of sam ples. Fig. 1 (a) shows an atom ic force m icroscopy (AFM) in age of a (5 5) m² surface area of the blind hole sam ple. The lateral size (b = 0.8 m) of



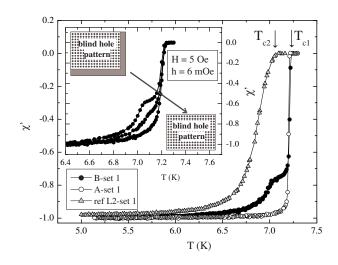


FIG.2: Screening ⁰ as function of tem perature T for set 1 of Pb lm swith an array of antidots (A, open circles), blind holes (B, lled circles) and a reference plain Pb lm with the same thickness as layer L2 (triangles), with H = 50e, f = 3837 Hz and h = 6 m Oe. Inset: ⁰ as function of T measured on blind hole sample B with the plain Pb contour progressively rem oved.

FIG.1: (a) A tom ic force m icrograph (AFM) of a $(5 \quad 5) m^2$ area of a Pb lm with a square array of square blind holes. (b) Schem atic cross section of the patterned superconducting sam ples studied in this work, a blind hole sam ple B and an antidot sam ple A. The two evaporated Pb layers L1 and L2 are indicated.

the holes and the period of the square array (d = 1.5 m) are identical for all used samples. The periodicity of the square lattice corresponds to a rst matching eld of H₁ = $_0$ =d² = 9.2 Oe. Here $_0$ is the ux quantum.

B. Superconducting properties

The ac-m agnetization m easurem ents were carried out in a commercialQ uantum Design PPM S-system with the ac-eld h parallel to the dc-eld H and both applied perpendicular to the sample surface. This system provides a temperature stability better than 0.5 m K which is crucial form easurem ents near the critical temperature. The ac-amplitude h ranges from $2 \text{ m O} \text{ e to } 15 \text{ O} \text{ e and the fre$ quency f from 10 Hz to 10 kHz. Since in this range offrequencies we observe that depends only weakly on f,we have chosen the sam e frequency f = <math>3837 Hz for all m easurem ents presented in this paper.

In order to characterize the physical properties of the di erent patterned $\ln s w e$ rst analyze the temperature dependence of the ac-susceptibility = $^{0} + ^{00}$. The result of these m easurements for set 1 of samples is shown in the main panel of Fig.2 at H = 50 e and h = 6 m 0 e. The data presented in this gure have been normalized by a factor corresponding to the maximum screening, such that $^{0} = 1$ at very low temperatures and elds. It can be seen that the 0 (T) curve for the antidot sam - ple A (open circles) shows a very sharp superconducting

transition at $T_{c1} = 7.22$ K. In contrast to that, the 0 (T) data for blind hole sam ple B (led circles) rst exhibits a sharp transition at T_{c1} followed by a second broader transition at $T_{c2} = 7.10$ K, below which it smoothly approaches to the maximum screening. In Fig. 2 we also include the superconducting transition corresponding to a non-patterned plain Pb Im (triangles) with the same thickness as layer L2 and evaporated simultaneously with sam ples A and B. The superconducting transition of this Im coincides with the onset of the second step on sam ple

в.

The origin of this two-step transition in the blind hole sam ple com es from a very narrow Pb border surrounding the blind hole pattern as a result of the fabrication procedure. Since the ac-response is mainly given by the border of the sam ple, a substantial enhancem ent of the screening at T_{c2} is expected when this Pb contour turns to the superconducting state, in agreem ent with our observation. In order to test this, we perform 0 (T) measurements on a sim ilar sam ple while progressively rem oving the plain Pb contour, as shown in the inset of Fig. 2. Now, it can be clearly seen that the transition at T_{c2} rst becomes broader and nally disappears after completely rem oving the plain Pb border. A lthough this undesirable contour may be eventually cut out, it helps to determ ine the critical tem perature of Pb layer L2 without preparing an extra plain Im. In this case, special care has to be taken in the norm alization process since the total saturation value at low tem peratures results from both, the patterned and the unpatterned areas.

Let us now compare the ux pinning properties of the blind hole array with those obtained for the antidot array. To that end we have carried out measurements of the acresponse in samples A and B as a function of dc-eld under isothermal conditions and xed ac-excitations. This is shown in the main panel of Fig. 3 for h = 0.23 Oe, $T = T_{c2} = 7.10$ K and f = 3837 Hz. In agreement with previous reports,^{2,3,4,14} the antidot sample A (open symbols) exhibits clear periodic matching features at integer and rationalmultiples of the rst matching eld H₁. A swe have discussed in an earlier work,¹⁴ two di erent regimes can be distinguished in this curve. At low elds $H < H_3$, a multi-quanta vortex state exists and matching features appear as small steps of the screening ⁰. For

elds H > H₃ the lled pinning sites become repulsive centers and entering vortices locate in the interstitial positions. In this regime, vortex-vortex interaction leads to highly stable vortex con gurations at H_n thus resulting in local enhancements of the screening $^{\rm O}({\rm H})$. We have also show n¹⁴ that the sharp reduction in the screening at H₄ can be attributed to the higher sensitivity of the ac-susceptibility in that particular range of eld penetration.

A swe have pointed out above, the analysis of the blind hole sample is a more subtle procedure since the signal normalization can be derived either from the saturation value corresponding to the second transition. For example, data taken at $T > T_{c2}$, where only the patterned Im contributes to the signal, should be norm alized using the saturation value obtained by extrapolating the rst transition $\begin{pmatrix} 0 \\ 0 \end{pmatrix}$, as shown with a dotted line in the inset of Fig. 3. A di erent norm alization value could be obtained due to proximity e ects which lead to a larger e ective sample size and consequently to a higher saturation. How ever, no substantial change of T_c has been detected, suggesting that the proximity e ect is not relevant. In any case, the correct norm alization value will lay between the two extreme values $\begin{bmatrix} 0 \\ 0 \end{bmatrix}$ and $\frac{02}{0}$, indicated by black arrows in the inset of Fig. 3. The result of this norm alization procedure is shown as a continuous curve in the main panel of Fig. 3, whereas the extrem es obtained by normalizing with $\begin{array}{c} 0 \\ 0 \end{array}$ and $\begin{array}{c} 0 \\ 0 \end{array}$ are shown as a gray painted area. The saturation value $_{0}^{0}$ can be also estimated as $_{0}^{0} = \frac{V}{4(1)}$ where V [cm³] is the volume of the sample and the dem agnetization factor.^{15,16} For this particular sam ple with lateral dim ensions w_1 and w_2 and thickness , $V = w_1$ W 2 10^{-7} cm 3 and 13:8 10⁵, so 4:7 $\frac{1}{w_1} + \frac{1}{w_2}$ 9.8 10⁴ emu/G which is very close to the exper-0 in ental value $\frac{02}{0} = 9:7 \quad 10^{-4}$ em u/G. Regardless the chosen norm alization, we can clearly see that com m ensurability features are also present in the blind hole sam ple.

A direct comparison of the (H) curves for sam ples A and B allows us to identify two clear di erences. First, the overall screening is lower for sam ple B, indicating

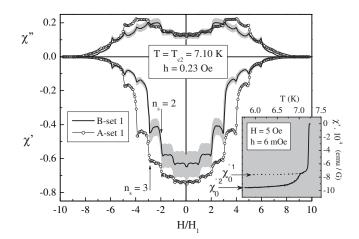


FIG.3: Screening 0 and dissipation 00 for $\ln s$ of set 1 with an array of antidots (open circles) and blind holes (thick solid line) as function of H=H $_{1}$ for T = $T_{\rm c2}$ = 7:10 K and h = 0:23 O e. The inset shows the 0 (T) transition for blind hole sample B, indicating the two possible saturation values used in the norm alization of the signal 0 .

that blind holes provide a less e cient pinning. This effect can be intuitively understood by considering the two extreme limits of very shallow blind holes (plain lm) where only intrinsic defects pin the vortices, and very deep blind holes (antidots) with a much stronger pinning force. W ithin this picture, it is expected that the e ective pinning force grows continuously as the thickness of the bottom layer decreases. The second point to consider is that $n_s = 2$ for blind holes whereas $n_s = 3$ for antidots (see black arrows in the main panel of Fig. 3). The same di errence in n_s was found by perform ing dcm agnetization m easurem ents on the sam e set of sam ples. This result is consistent with previous Bitter decoration experiments⁸ showing that the dierence between the saturation number of blind holes and antidots does not exceed one.

The origin of these di erences can be attributed to the pinning nature of blind holes and antidots. Indeed, the interaction of a ux line with a blind hole substantially di ers from the more widely investigated vortex-antidot interaction. In both cases, the norm al/superconductor boundary im poses a condition to the supercurrents to

ow parallel to the boundary of the hole. This e ect can be modelled by introducing an image antivortex inside the hole which interacts attractively with the ux line¹⁷ For the antidots, this attractive force acts along the total length of the ux line, whereas for blind holes we expect, as a rst approximation, a smaller force proportional to the depth of the hole. This scenario becomes more com – plicated when considering the interaction of a ux line with an occupied blind hole. In this case, whereas ux quanta trapped by an antidot consist of supercurrents owing around the hole, ux quanta pinned by blind

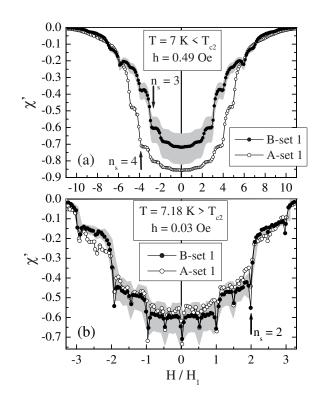


FIG.4: Screening 0 as function of H =H $_{1}$ for Pb $\,$ Im s of set 1 with an array of blind holes (lled symbols) and antidots (open symbols) with (a) T = 7K < T_{\rm c2} and h = 0:49 Oe and (b) T = 7:18K > T_{\rm c2} and h = 0:03 Oe.

holes remain as separated single-quanta ux lines with a well de ned core. Now an external vortex outside of the blind hole would simultaneously feel attraction due to the image antivortex and repulsion due to the trapped vortex. Besides that, the stray eld produced by vortices inside the blind holes can not spread out freely in space since it has to be screened by the inner edges of the hole, this leads to an extra term in the interaction. For higher

llings, trapped ux lines are able to rearrange inside the blind hole, a degree of freedom absent in antidots. The repulsive interaction between these single-quanta vortices m ight explain the origin of the lower saturation number observed for the blind hole sam ple.

Let's now m ove on to the analysis of the ac-response for tem peratures above and below the critical tem perature, T_{c2} of the bottom layer. For $T < T_{c2}$, as expected, we observe the same di erent ux pinning properties for blind holes and antidots, as is shown in Fig. 4 (a) for T=7~K. For $T>T_{c2}$, an isolated plain Pb $\,$ m with the same thickness as layer L2 is in the normal state (see Fig. 2). A lthough this $\,$ m L2 form s the bottom layer of the blind holes, in this case it is not isolated but rather surrounded by the superconducting Pb bilayer which m ay induce superconductivity. Therefore, in this speci c tem perature region we expect that the pinning behavior of blind holes

asymptotically approaches that of the antidots. This is indeed con med by the data shown in Fig.4(b) for the same set of samples at T = 7.18 K. The most obvious feature of this gure is the similarity between the acresponse of both samples, i.e. similar ac-shielding and the same saturation number. All the observations re-

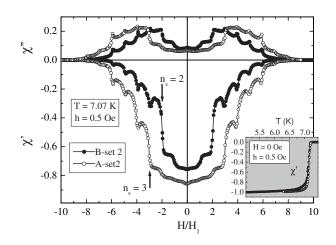


FIG.5: Screening ⁰ and dissipation ⁰⁰ as function of $H = H_1$, for Pb lms of set 2 with an array of antidots (open circles) and blind holes (lled circles) for T = 7:07 K, f = 3837 Hzand h = 0.50 e. The inset shows the temperature dependence of the normalized screening ⁰ for the samples A and B.

ported for set 1 of sam ples were also reproduced for set 2 of sam ples. These results are shown in Fig. 5. In this case, sam ple A and B have the sam e $T_{\rm c}$ = 7.22 K, as is shown in the inset of Fig. 5.

An alternative way to investigate the pinning properties of blind holes and antidots is to analyze the di erent ac vortex dynam ic regim es.^{18,19} For very low ac-drives, all vortices oscillate inside the corresponding individual pinning potentials. This so-called linear regime is characterized by an h-independent screening together with a very low dissipation.^{20,21} As the ac-drive is increased, vortices eventually overcom e the pinning well switching to a more dissipative regime with an h-dependent screening. The boundary between these two regimes is mainly determ ined by the strength of the pinning centers. Consequently, the stronger the pinning, the larger the extension of the linear regime. Experimentally, a reliable criterium to determ ine the onset of non-linearity is given by a dissipation $^{(0)}(h) = 0.05$ as is shown in Fig. 6(a) for sam ple A of set 1 at several tem peratures. Perform ing this procedure for sam ples A and B, we can com pare the dynam ic diagram sh (T) of antidot and blind hole sam ples (see Fig. 6(b)). Most obvious in Fig. 6(b) is the smaller extension of the linear regime for the blind hole sample B. This is a clear indication that the blind hole array produces a weaker pinning potential, in agreem ent with our previous observations. In addition, for tem peratures $T > T_{c2}$, the two boundaries collapse on a single line.

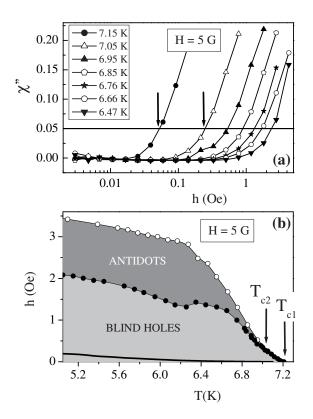


FIG.6: (a) D issipation ⁽⁰⁾ as function of the ac-ekl h for an array of antidots at several T, f = 3837 H z and H = 5 O e. A rrow s indicate the onset of the non-linear response according to the chosen criterium ⁽⁰⁾ = 0.05 (horizontal line). (b) P hase boundary of the linear regime for sam ples A and B of set 1, for H = 5 O e and f = 3837 H z. This boundary is obtained using a dissipation criterium ⁽⁰⁾ = 0.05 as shown in (a) for antidot sam ple A. The continuous line indicates the boundary of the linear regime for a reference non-patterned Pb Im with the same thickness as layer L2.

This result is consistent with the fact that for $T > T_{\rm c2}$ the thin layer at the bottom of the blind holes approaches to a norm alm etal, thus turning to the behavior of the antidot sample. Fig. 6 (b) also includes the dynam ic diagram h (T) for a reference lm with the same thickness as layer L2. As expected, the very low e ective pinning of the plain lm results in a substantial sm aller extension of the linear regime in comparison with the patterned samples A and B.

It is important to stress that there is also a di erence in the depinning process of vortices trapped by antidots and blind holes. On one hand, single-quanta vortices trapped by the blind holes are able to depin one by one. On the other hand, as has been pointed out by Priour and Fertig²² in the case of multiquanta vortices (without rigid core) trapped by antidots, the driving current elongates the vortex core which can eventually reach the neighbor pinning site thus allowing the vortex to hop from site to site. A llthese considerations should be taken into account in order to theoretically analyze the pinning properties of blind holes.

IV. CONCLUSION

We have used ac-susceptibility to perform a comparative study of the ux pinning properties of an array of antidots and blind holes. W e show that antidots are m ore e cient pinning centers than blind holes where the superconducting Im is not fully perforated. Consequently, a reduced screening for the blind hole system is observed. Therefore, the strength of the pinning potential can be gradually tuned by varying the depth of blind holes. On top of that, the saturation number $n_{\rm s},\,de\,$ ned as the maximum number of ux quanta that a pinning site can hold, is higher for antidots than for blind holes, in agreem ent with previous reports. The linear regime, in which vortices oscillate inside the pinning potential, has a smaller extension for the blind hole sample, indicating that blind holes provide a weaker pinning potential. Finally, we discussed the ac-response for tem peratures above the critical tem perature of the bottom layer and found that the pinning behavior of blind holes approaches the behavior of antidots.

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